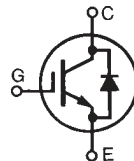


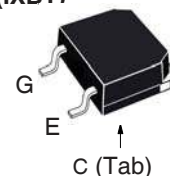
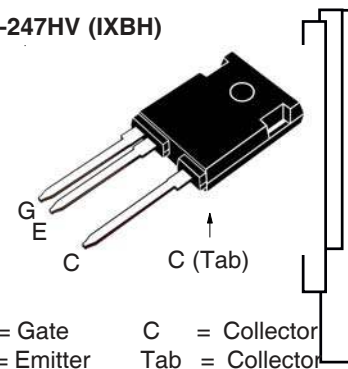
**High Voltage, High Gain
BIMOSFET™ Monolithic
Bipolar MOS Transistor**
**IXBT20N360HV
IXBH20N360HV**


$$V_{CES} = 3600V$$

$$I_{C110} = 20A$$

$$V_{CE(sat)} \leq 3.4V$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	3600	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	3600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	70	A
I_{C110}	$T_C = 110^\circ C$	20	A
I_{CM}	$T_C = 25^\circ C$, 1ms	220	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 160$ $V_{CES} \leq 1500$	A V
T_{SC} (SCSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 52\Omega$, $V_{CE} = 1500V$, Non-Repetitive	10	μs
P_C	$T_C = 25^\circ C$	430	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247HV)	1.13/10	Nm/lb.in
Weight	TO-268HV	4	g
	TO-247HV	6	g

TO-268HV (IXBT)

TO-247HV (IXBH)


G = Gate C = Collector
E = Emitter Tab = Collector

Features

- High Voltage Packages
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	3600		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			25 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 20A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		2.9 3.6	3.4 V V

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Symbol	Test Conditions	Characteristic Values			Units
		Min.	Typ.	Max.	
g_{fs}	$I_C = 20\text{A}, V_{CE} = 10\text{V}$, Note 1	10	17		S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2045		pF
C_{oes}			110		pF
C_{res}			50		pF
$Q_{g(on)}$	$I_C = 20\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		110		nC
Q_{ge}			13		nC
Q_{gc}			43		nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1500\text{V}, R_G = 10\Omega$ Note 2		18		ns
t_{ri}			14		ns
E_{on}			15.50		mJ
$t_{d(off)}$			238		ns
t_{fi}			206		ns
E_{off}			4.30		mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1500\text{V}, R_G = 10\Omega$ Note 2		20		ns
t_{ri}			22		ns
E_{on}			16.10		mJ
$t_{d(off)}$			247		ns
t_{fi}			216		ns
E_{off}			4.15		mJ
$t_{d(on)}$	Resistive load, $T_J = 25^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 10\Omega$		30		ns
t_r			325		ns
$t_{d(off)}$			165		ns
t_f			1045		ns
$t_{d(on)}$	Resistive load, $T_J = 125^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 960\text{V}, R_G = 10\Omega$		32		ns
t_r			890		ns
$t_{d(off)}$			185		ns
t_f			1100		ns
R_{thJC}				0.29	$^\circ\text{C/W}$
R_{thCS}	TO-247HV	0.21			$^\circ\text{C/W}$

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Symbol	Test Conditions	Characteristic Values			Units
		Min.	Typ.	Max.	
V_F	$I_F = 20\text{A}, V_{GE} = 0\text{V}$, Note 1			3.5	V
t_{rr}	$I_F = 10\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GE} = 0\text{V}$		1.7		μs
I_{RM}			35		A
Q_{RM}			30		μC

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

ADVANCE TECHNICAL INFORMATION

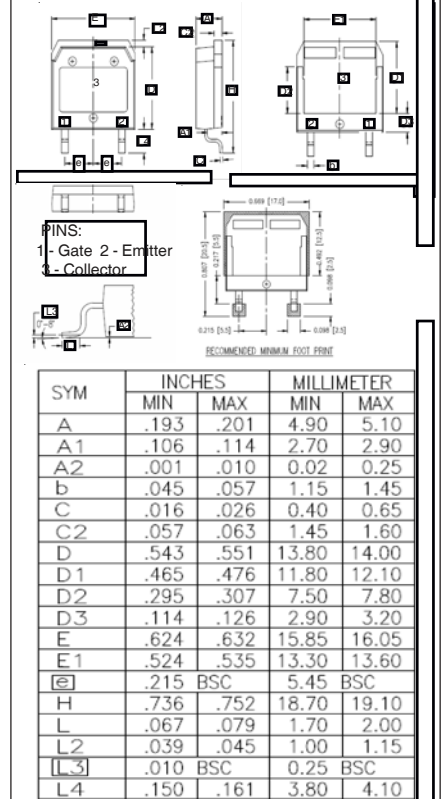
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-268HV Outline



TO-247HV Outline

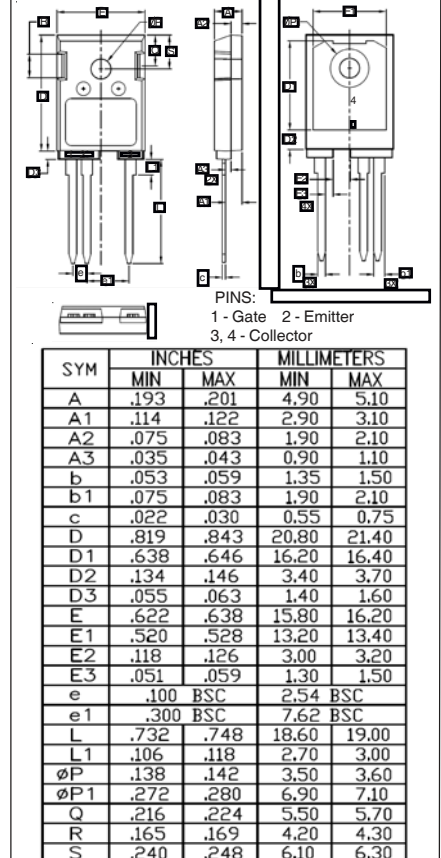


Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

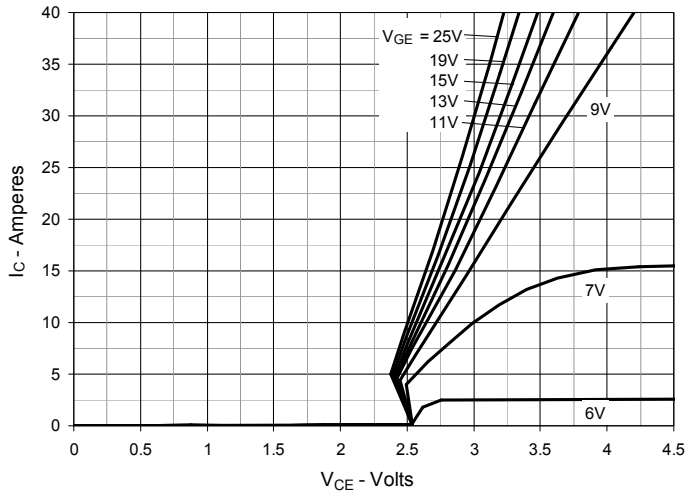


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

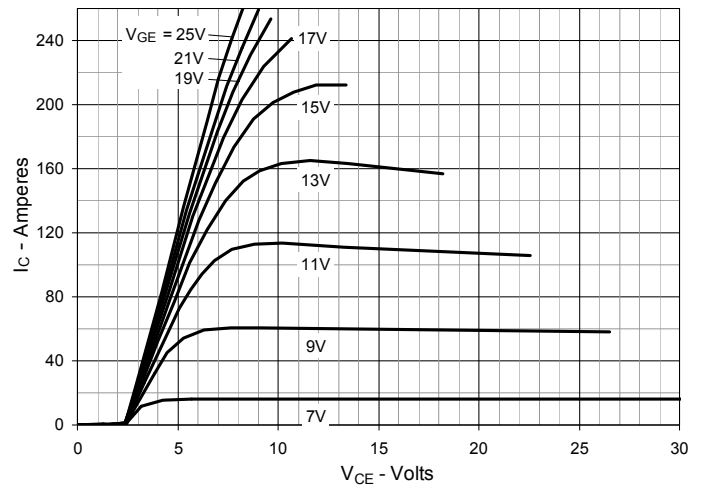


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

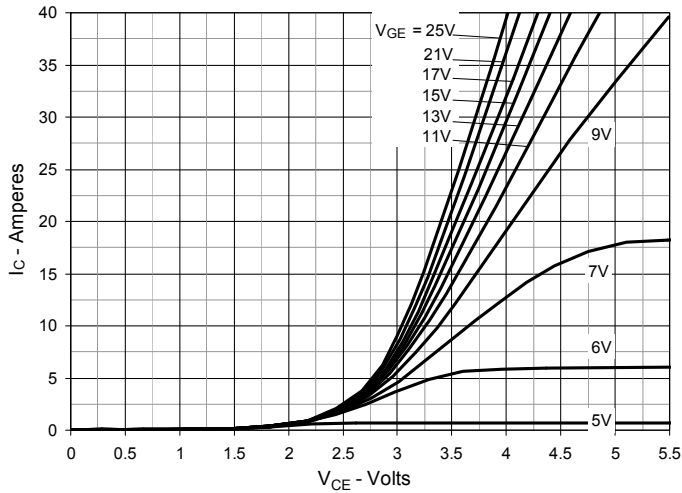


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

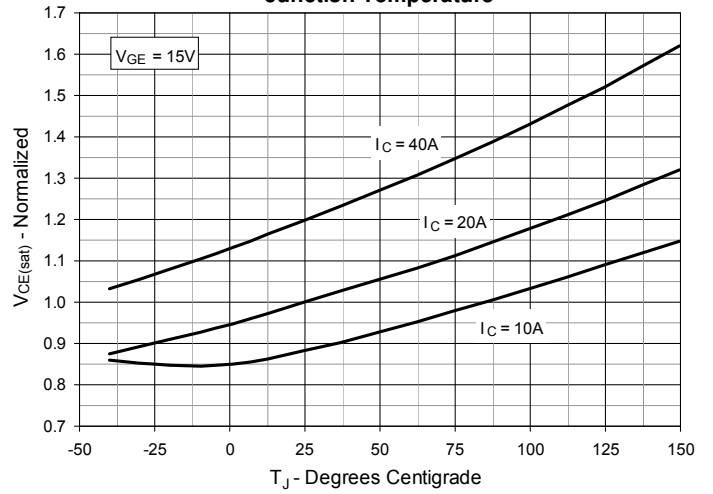


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

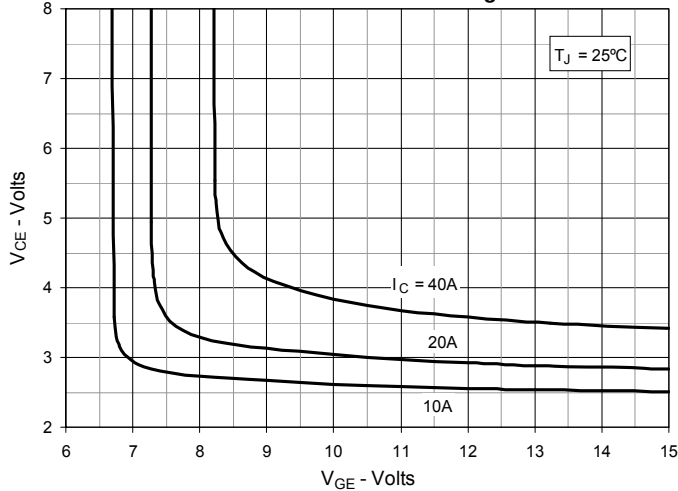


Fig. 6. Input Admittance

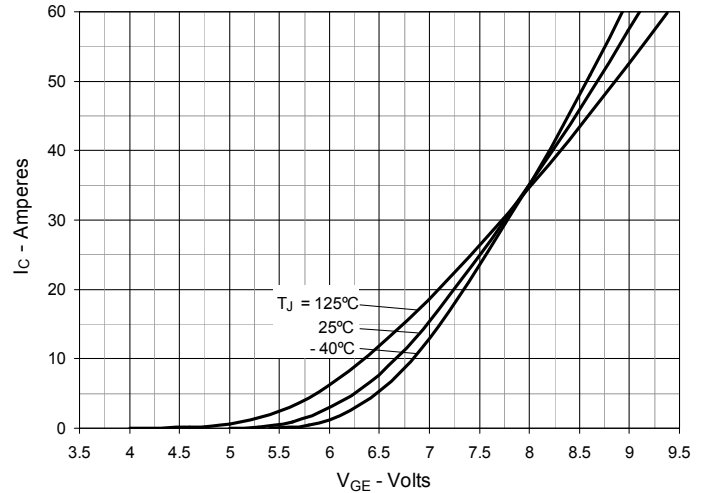


Fig. 7. Transconductance

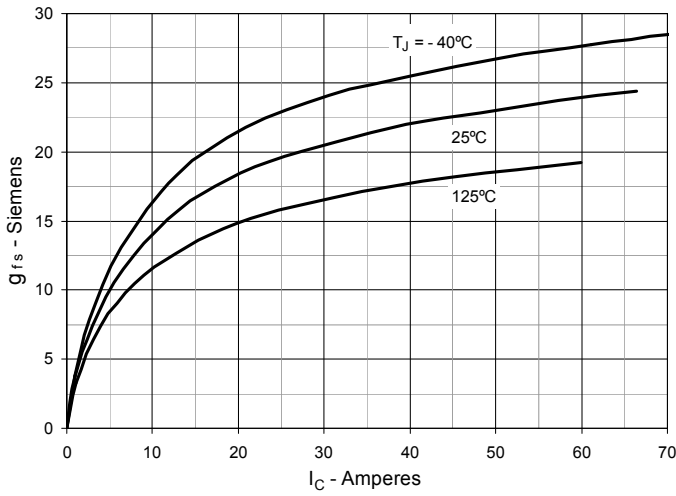


Fig. 8. Gate Charge

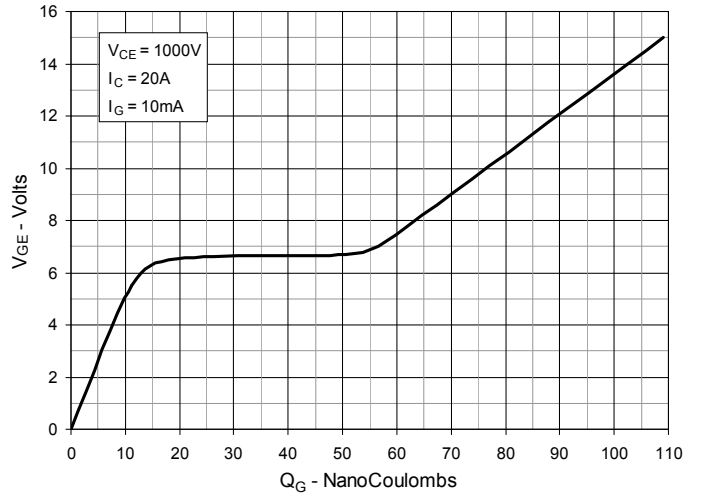


Fig. 9. Forward Voltage Drop of Intrinsic Diode

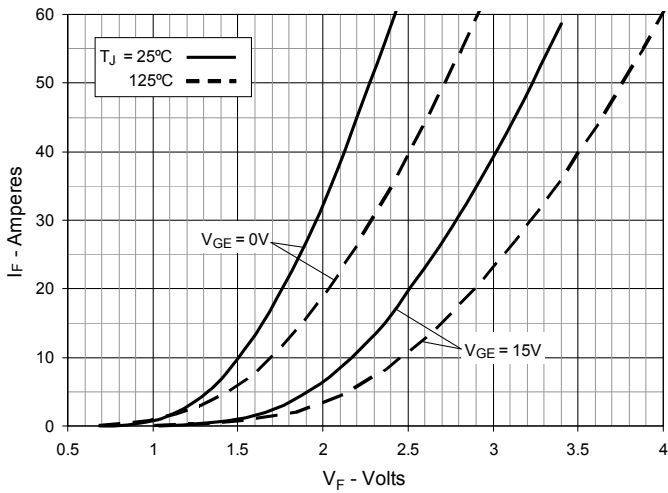


Fig. 10. Capacitance

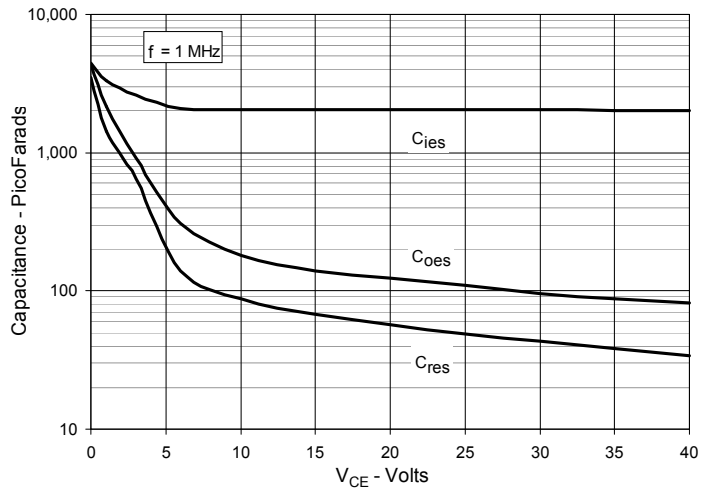


Fig. 11. Reverse-Bias Safe Operating Area

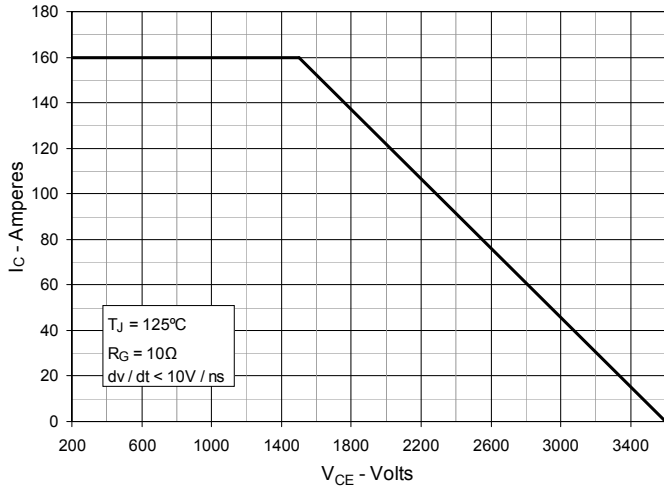


Fig. 12. Maximum Transient Thermal Impedance

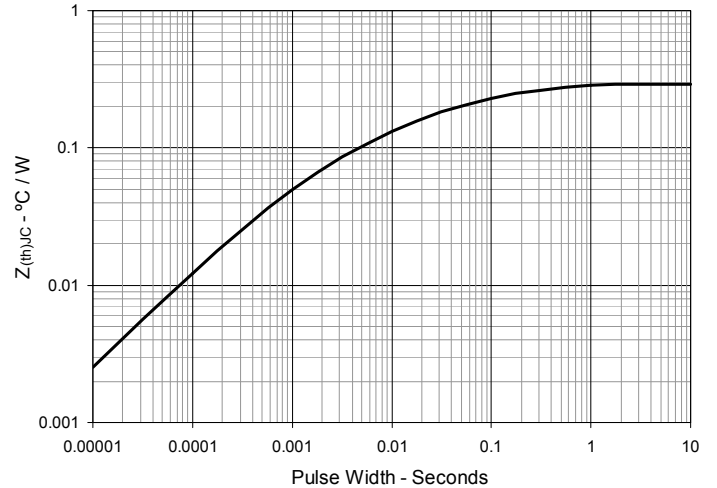


Fig. 13. Forward-Bias Safe Operating Area @ $T_C = 25^\circ\text{C}$

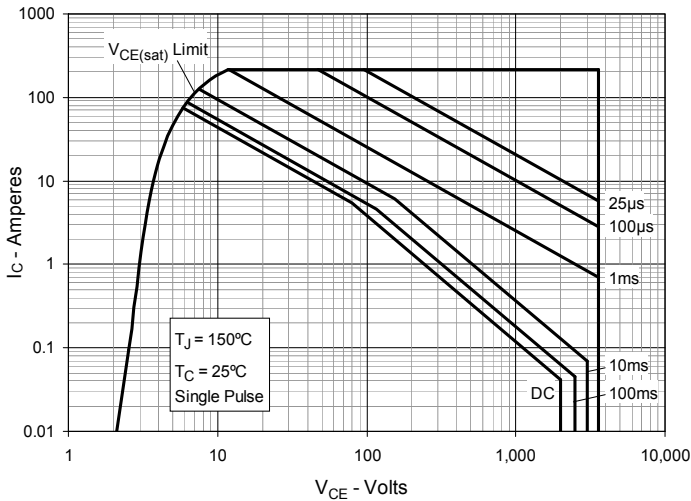


Fig. 14. Forward-Bias Safe Operating Area @ $T_C = 75^\circ\text{C}$

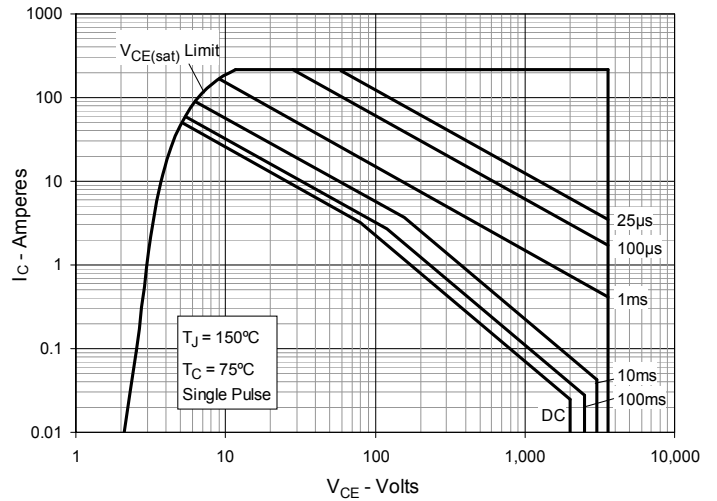


Fig. 15. Inductive Switching Energy Loss vs. Gate Resistance

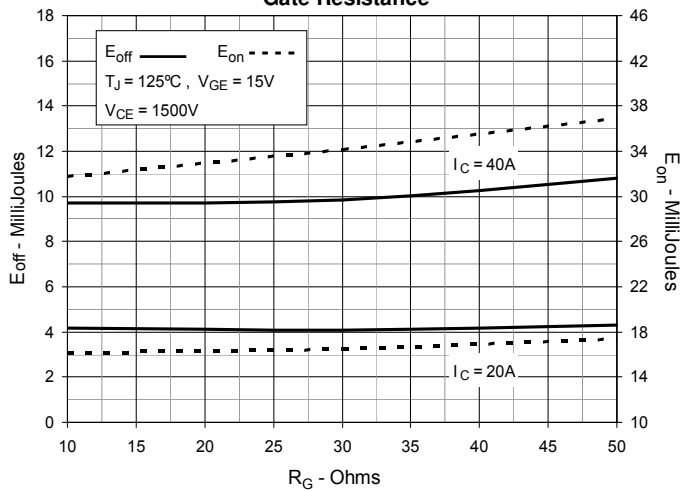


Fig. 16. Inductive Switching Energy Loss vs. Collector Current

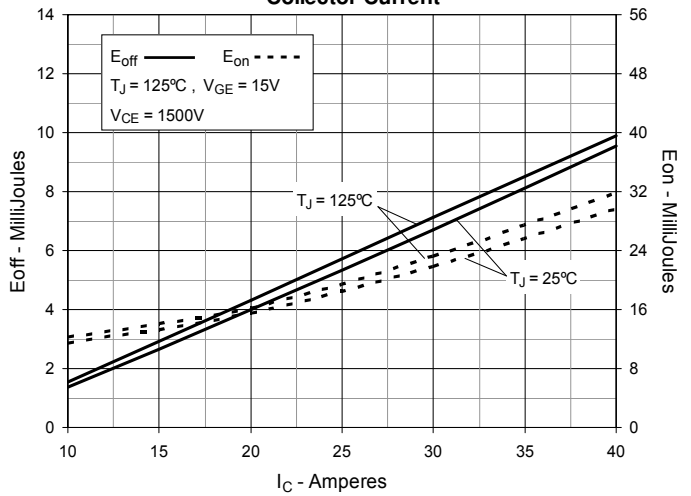


Fig. 17. Inductive Switching Energy Loss vs. Junction Temperature

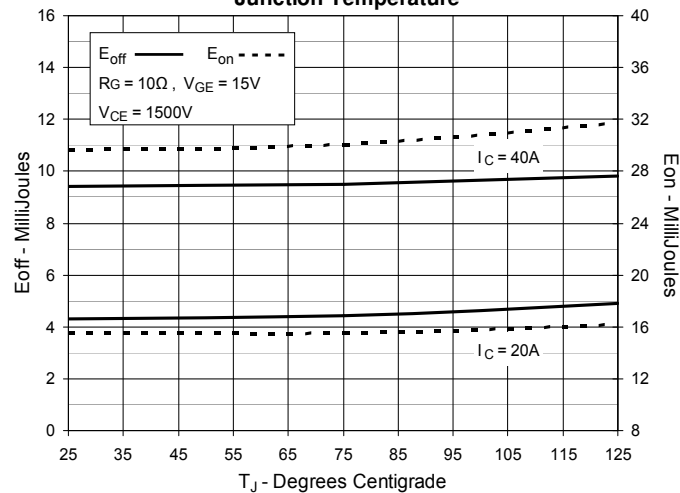


Fig. 18. Inductive Turn-off Switching Times vs. Gate Resistance

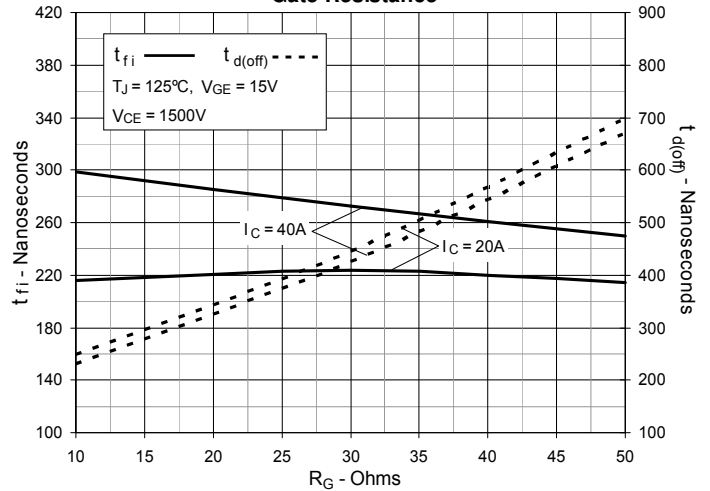


Fig. 19. Inductive Turn-off Switching Times vs. Collector Current

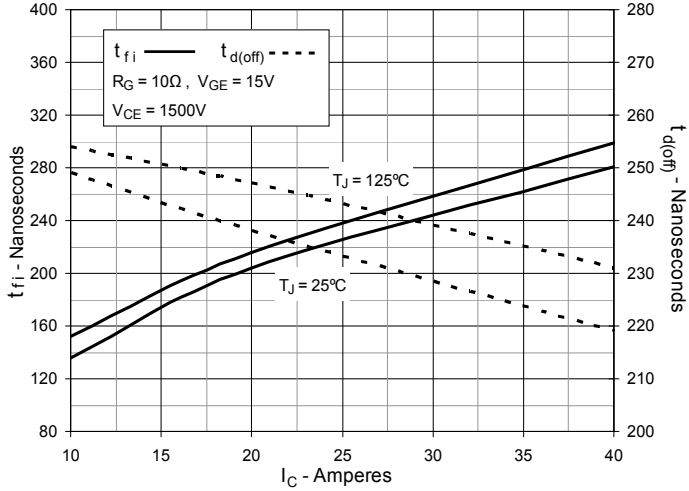


Fig. 20. Inductive Turn-off Switching Times vs. Junction Temperature

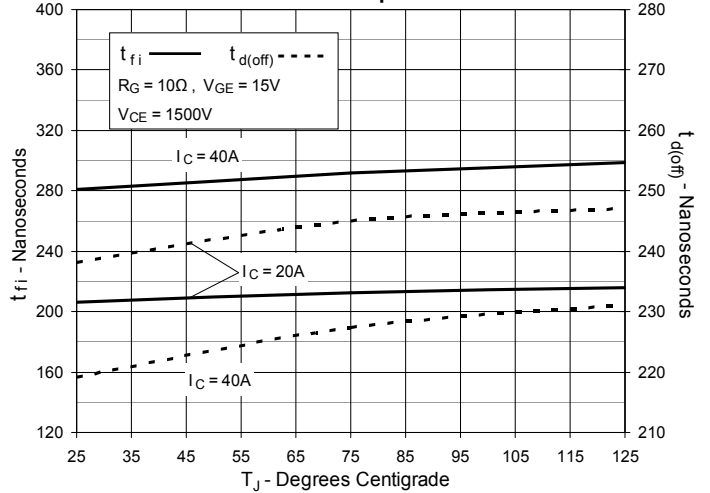


Fig. 21. Inductive Turn-on Switching Times vs. Gate Resistance

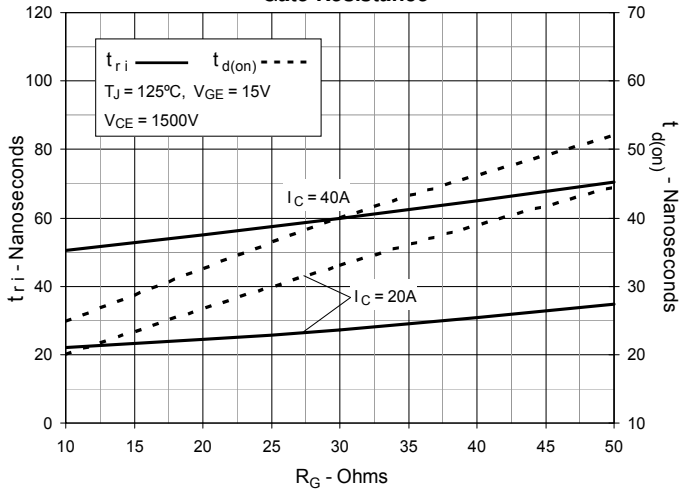


Fig. 22. Inductive Turn-on Switching Times vs. Collector Current

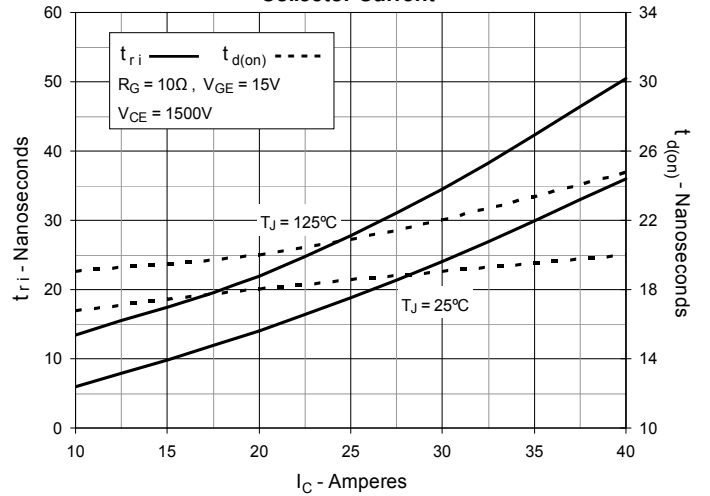
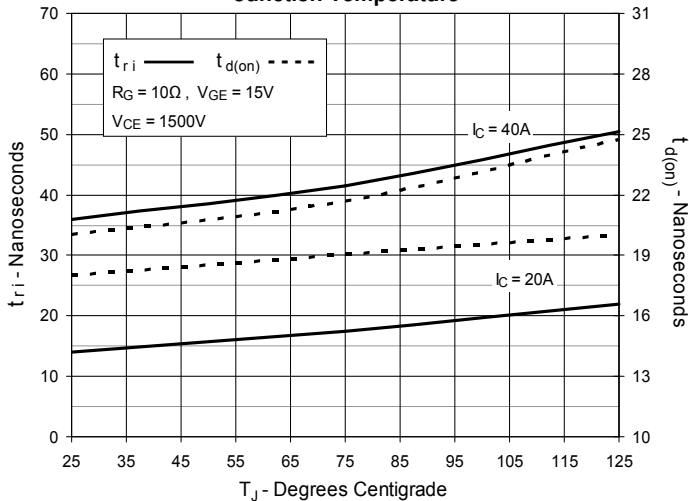


Fig. 23. Inductive Turn-on Switching Times vs. Junction Temperature





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